Applications Note:SY58203

Single Stage Flyback And PFC Regulator With Primary Side Control For LED Lighting

Preliminary datasheet

General Description

The SY58203 is a single stage Flyback and PFC regulator targeting at LED lighting applications. It integrates a 700V MOSFET to decrease physical volume. It is a primary side controller without applying any secondary feedback circuit for low cost, and drives the Flyback converter in the quasi-resonant mode to achieve higher efficiency. It keeps the Flyback converter in constant on time operation to achieve high power factor.

Features

- Integrated 700V MOSFET
- Primary side control eliminate to the opto-coupler.
- Valley turn-on of the primary MOSFET to achieve low switching losses
- 0.3V primary current sense reference voltage leads to a lower sense resistance thus a lower conduction loss.
- Low start up current: 15μA typical
- Reliable short LED and Open LED protection
- Power factor >0.90 with single-stage conversion.
- Maximum frequency limit: 120kHz
- Compact package: SO8

Ordering Information

SY58203□(□□)□

- Temperature Code
- Package Code
- Optional Spec Code

Temperature Range: -40°C to 105°C

Ordering Number	Package type	Note
SY58203FAC	SO8	----

Applications

- LED lighting

Recommended operating output power		
Products	90~264Vac	176~264Vac
SY58203	10W	17.5W

Typical Applications

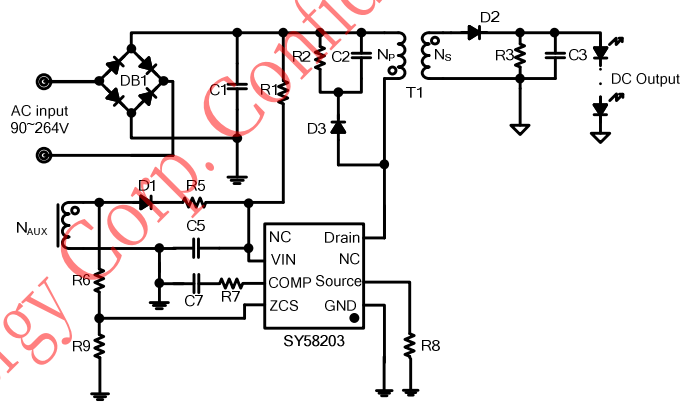


Figure 1. Schematic Diagram SO8

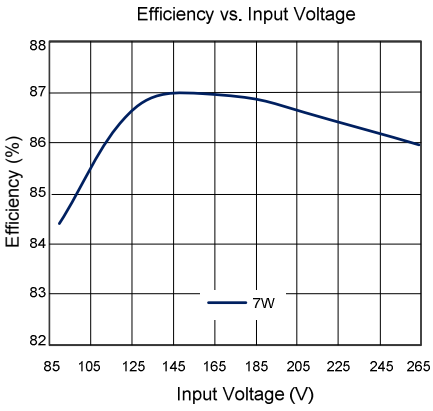
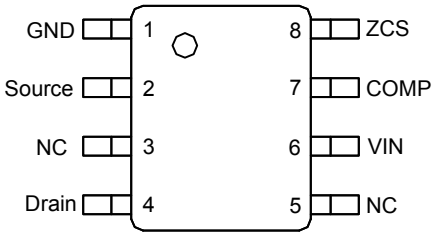


Figure 2. Efficiency vs Input Voltage

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Pinout (top view)



(SO8)

Top Mark: AGF *xyz* (device code: AGF, ***x=year code, y=week code, z= lot number code*****)**

Pin Name	Pin number SO8	Pin Description
GND	1	Ground pin
Source	2	Source pin of the internal primary MOSFET. Connect the sense resistor to this Pin and the GND pin. (current sense resister R_S: $R_S = k\frac{V_{REF} \times N_{PS}}{I_{OUT}}$, $k = 0.167$)
NC	3	
Drain	4	Drain of the internal power MOSFET.
NC	5	
VIN	6	Power supply pin. This pin also provides output over voltage protection along with ZCS pin.
COMP	7	Loop compensation pin. Connect a RC network across this pin and ground to stabilize the control loop.
ZCS	8	Inductor current zero-crossing detection pin. This pin receives the auxiliary winding voltage by a resister divider and detects the inductor current zero crossing point. This pin also provides over voltage protection and line regulation modification function simultaneously. If the voltage on this pin is above $V_{ZCS,OVP}$, the IC would enter over voltage protection mode. Good line regulation can be achieved by adjusting the upper resistor of the divider.

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Absolute Maximum Ratings (Note 1)

VIN ---------- -0.3V to 19V
Supply current I_{VIN} ---------- 30mA
ZCS ---------- -0.3V to V_{IN}+0.3V
COMP,Source ---------- -0.3V to 3.6V
Drain ---------- 700V
Power Dissipation, @ T_A = 25°C SO8 ---------- 1.1W
Package Thermal Resistance (Note 2)
SO8, θ JA ---------- 88°C/W
SO8, θ JC ---------- 45°C/W
Temperature Range ---------- -40°C to 150°C
Lead Temperature (Soldering, 10 sec.) ---------- 260°C
Storage Temperature Range ---------- -65°C to 150°C

Recommended Operating Conditions (Note 3)

VIN ---------- 8V~15.4V
Junction Temperature Range ---------- -40°C to 125°C
Ambient Temperature Range ---------- -40°C to 105°C

Block Diagram

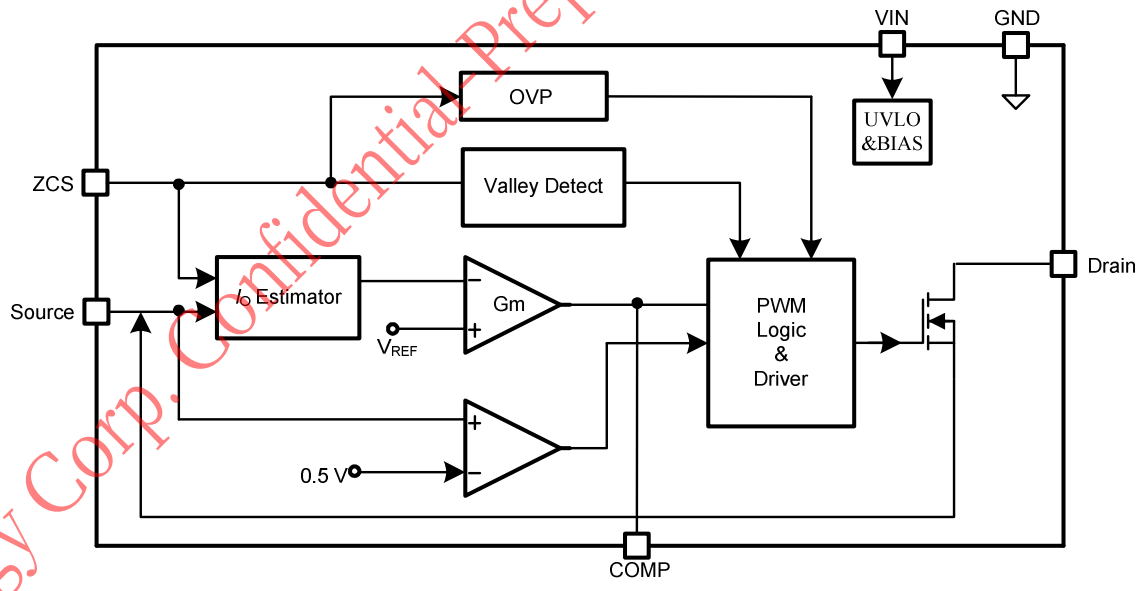


Figure3. Block Diagram

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Electrical Characteristics

(V_{IN} = 12V (Note 3), T_A = 25°C unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Power Supply Section						
Input voltage range	V_{VIN}		8		15.4	V
VIN turn-on threshold	$V_{VIN,ON}$				17.6	V
VIN turn-off threshold	$V_{VIN,OFF}$		6.0		7.9	V
VIN OVP voltage	$V_{VIN,OVP}$			V_{VIN_ON}+0.85		V
Start up Current	I_{ST}	V_{VIN}<$V_{VIN,OFF}$		15		µA
Operating Current	I_{VIN}	C_L=100pF,f=15kHz		1		mA
Shunt current in OVP mode	$I_{VIN,OVP}$	V_{VIN}>$V_{VIN,OVP}$	1.6	2	2.5	mA
Error Amplifier Section						
Internal reference voltage	V_{REF}		0.294	0.3	0.306	V
ZCS pin Section						
ZCS pin OVP voltage threshold	$V_{ZCS,OVP}$		1.41	1.48	1.55	V
Integrated MOSFET Section						
Breakdown Voltage	V_{BV}	V_{GS}=0V,I_{DS}=250µA	700			V
Current Sense Section(Source pin of integrated MOSFET)						
Current limit reference voltage	$V_{Source,MAX}$			0.50		V
PWM Section						
Max ON Time	$T_{ON,MAX}$	V_{COMP}=1.5V		24		µs
Min ON Time	$T_{ON,MIN}$			400		ns
Max OFF Time	$T_{OFF,MAX}$			39		µs
Min OFF Time	$T_{OFF,MIN}$			2		µs
Maximum switching frequency	f_{MAX}			120		kHz
Thermal Section						
Thermal Shutdown Temperature	T_{SD}			150		°C

Note 1: The recommended power is measured by 25°C temperature rise on case, in an open frame design with adequate heat sinking.

Note 2: Stresses beyond the "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only. Functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Note 3: θ_{JA} is measured in the natural convection at T_A = 25°C on a low effective single layer thermal conductivity test board of JEDEC 51-3 thermal measurement standard. Test condition: Device mounted on 2" x 2" FR-4 substrate PCB, 2oz copper, with minimum recommended pad on top layer and thermal vias to bottom layer ground plane.

Note 4: Increase VIN pin voltage gradually higher than $V_{VIN,ON}$ voltage then turn down to 12V.

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Operation

The SY58203 is a single stage Flyback and PFC regulator targeting at LED lighting applications.

It integrates a 700V MOSFET to decrease physical volume.

The device provides primary side control to eliminate the opto-couplers or the secondary feedback circuits, which would cut down the cost of the system.

High power factor is achieved by constant on operation mode, with which the control scheme and the circuit structure are both simple.

In order to reduce the switching losses and improve EMI performance, Quasi-Resonant switching mode is applied, which means to turn on the integrated MOSFET at voltage valley; the start up current of SY58203 is rather small (15μA typically) to reduce the standby power loss further; the maximum switching frequency is clamped to 120kHz to reduce switching losses and improve EMI performance when the converter is operated at light load condition.

SY58203 provides reliable protections such as Short Circuit Protection (SCP), Open LED Protection (OLP), Over Temperature Protection (OTP), etc.

SY58203 is available with SO8 package.

Applications Information

Start up

After AC supply or DC BUS is powered on, the capacitor C_{VIN} across VIN and GND pin is charged up by BUS voltage through a start up resistor R_{ST}. Once V_{VIN} rises up to V_{VIN-ON}, the internal blocks start to work. V_{VIN} will be pulled down by internal consumption of IC until the auxiliary winding of Flyback transformer could supply enough energy to maintain V_{VIN} above $V_{VIN-OFF}$.

The whole start up procedure is divided into two sections shown in Fig.4. t_{STC} is the C_{VIN} charged up section, and t_{STO} is the output voltage built-up section. The start up time t_{ST} composes of t_{STC} and t_{STO}, and usually t_{STO} is much smaller than t_{STC}.

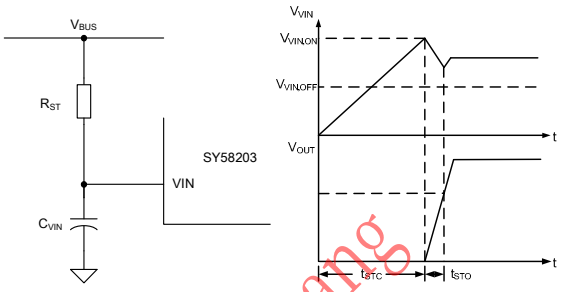


Fig.4 Start up

The start up resistor R_{ST} and C_{VIN} are designed by rules below:

(a) Preset start-up resistor R_{ST}, make sure that the current through R_{ST} is larger than I_{ST} and smaller than I_{VIN_OVP}

$$\frac{V_{BUS}}{I_{VIN_OVP}} < R_{ST} < \frac{V_{BUS}}{I_{ST}} \quad (1)$$

Where V_{BUS} is the BUS line voltage.

(b) Select C_{VIN} to obtain an ideal start up time t_{ST}, and ensure the output voltage is built up at one time.

$$C_{VIN} = \frac{(\frac{V_{BUS}}{R_{ST}} - I_{ST}) \times t_{ST}}{V_{VIN_ON}} \quad (2)$$

(d) If the C_{VIN} is not big enough to build up the output voltage at one time. Increase C_{VIN} and decrease R_{ST}, go back to step (a) and redo such design flow until the ideal start up procedure is obtained.

Internal pre-charge design for quick start up

After V_{VIN} exceeds $V_{VIN,ON}$, V_{COMP} is pre-charged by an internal current source. The PWM block won't start to output PWM signals until V_{COMP} is over the initial voltage $V_{COMP,IC}$, which can be programmed by R_{COMP}. Such design is meant to reduce the start up time shown in Fig.5.

The voltage pre-charged V_{COMP_IC} in start-up procedure can be programmed by R_{COMP}

$$V_{COMP_IC} = 600mV - 300\mu A \times R_{COMP} \quad (3)$$

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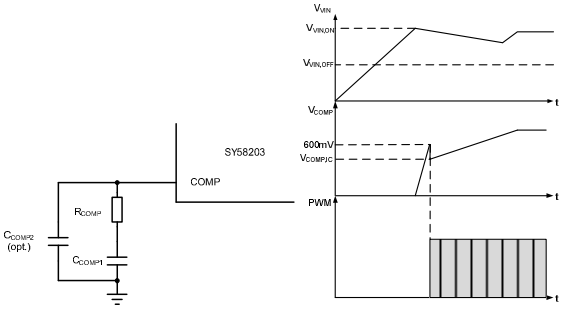


Fig.5 pre-charge scheme in start up

Where $V_{COMP-IC}$ is the pre-charged voltage of COMP pin.

Generally, a big capacitance of C_{COMP} is necessary to achieve high power factor and stabilize the system loop (1μF~2μF recommended); The voltage pre-charged in start-up procedure can be programmed by R_{COMP}; On the other hand, larger R_{COMP} can provide larger phase margin for the control loop; A small ceramic capacitor is added to suppress high frequency interruption (10pF~100pF is recommended if necessary)

Shut down

After AC supply or DC BUS is powered off, the energy stored in the BUS capacitor will be discharged. When the auxiliary winding of Flyback transformer can not supply enough energy to VIN pin, V_{VIN} will drop down. Once V_{VIN} is below $V_{VIN-OFF}$, the IC will stop working and V_{COMP} will be discharged to zero.

Primary-side constant-current control

Primary side control is applied to eliminate secondary feedback circuit or opto-coupler, which reduces the circuit cost. The switching waveforms are shown in Fig.6.

The output current I_{OUT} can be represented by,

$$I_{OUT}=\frac{I_{SP}}{2}\times\frac{t_{DIS}}{t_S}\ (4)$$

Where I_{SP} is the peak current of the secondary side; t_{DIS} is the discharge time of Flyback transformer; t_S is the switching period.

The secondary peak current is related with primary peak current, if the effect of the leakage inductor is neglected.

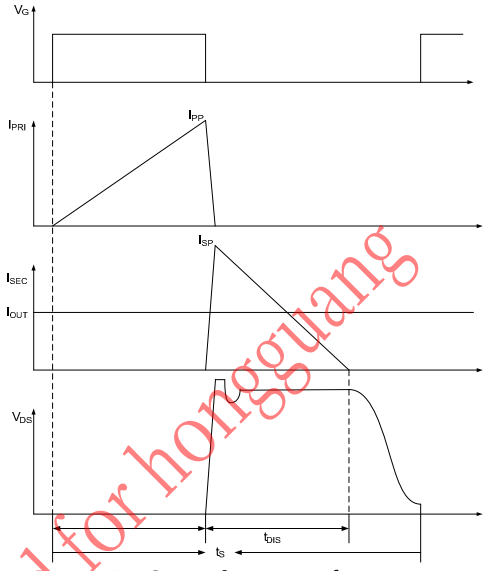


Fig.6 switching waveforms

$$I_{SP}=N_{PS}\times I_{PP}\ (5)$$

Where N_{PS} is the turns ratio of primary to secondary of the Flyback transformer.

Thus, I_{OUT} can be represented by

$$I_{OUT}=\frac{N_{PS}\times I_{PP}}{2}\times\frac{t_{DIS}}{t_S}\ (6)$$

The primary peak current I_{PP} and inductor current discharge time t_{DIS} can be detected by Source and ZCS pin, which is shown in Fig.7. These singals are processed and applied to the negative input of the gain modulator. In static state, the positive and negative inputs are equal.

$$V_{REF}=I_{PP}\times R_S\times\frac{t_{DIS}}{t_S}\times k_1\ (7)$$

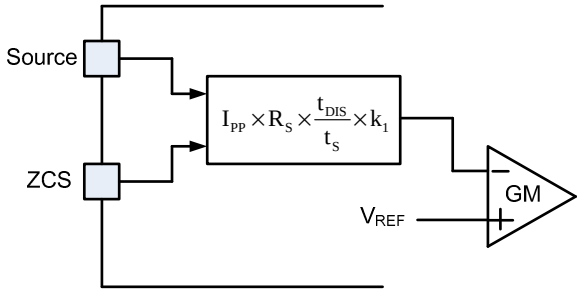


Fig.7 Output current detection diagram

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Finally, the output current I_{OUT} can represented by

$$I_{OUT}=\frac{V_{REF}\times N_{PS}}{R_S\times 2\times k_1} (8)$$

Where k_1 is the output current weight coefficient; V_{REF} is the internal reference voltage; R_S is the current sense resistor.

k_1, and V_{REF} are all internal constant parameters, I_{OUT} can be programmed by N_{PS} and R_S.

$$R_S=\frac{V_{REF}\times N_{PS}}{I_{OUT}\times 2\times k_1} (9)$$

then

$$R_S=\frac{k\times V_{REF}\times N_{PS}}{I_{OUT}},\ k=\frac{1}{2k_1} (10)$$

Quasi-Resonant Operation

QR mode operation provides low turn-on switching losses for Flyback converter.

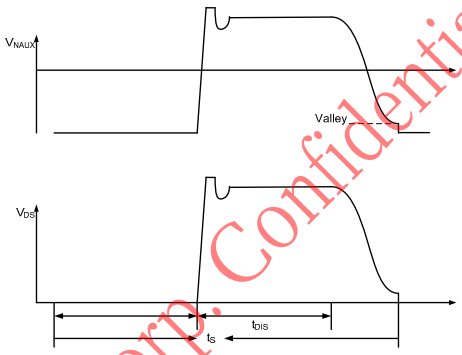


Fig.8 QR mode operation

The voltage across drain and source of the primary integrated MOSFET is reflected by the auxiliary winding of the Flyback transformer. ZCS pin detects the voltage across the auxiliary winding by a resistor divider. When the voltage across drain and source of the primary integrated MOSFET is at voltage valley, the MOSFET would be turned on.

Over Voltage Protection (OVP) & Open LED Protection (OLP)

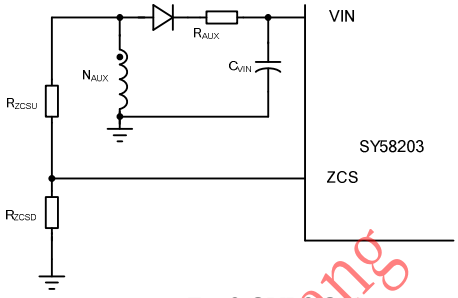


Fig.9 OVP&OLP

The output voltage is reflected by the auxiliary winding voltage of the Flyback transformer, and both ZCS pin and VIN pin provide over voltage protection function. When the load is null or large transient happens, the output voltage will exceed the rated value. When V_{VIN} exceeds $V_{VIN,OVP}$ or V_{ZCS} exceeds $V_{ZCS,OVP}$, the over voltage protection is triggered and the IC will discharge V_{VIN} by an internal current source $I_{VIN,OVP}$. Once V_{VIN} is below $V_{VIN,OFF}$, the IC will shut down and be charged again by BUS voltage through start up resistor. If the over voltage condition still exists, the system will operate in hiccup mode.

Thus, the turns of the auxiliary winding N_{AUX} and the resistor divider is related with the OVP function.

$$\frac{V_{ZCS_OVP}}{V_{OVP}}=\frac{N_{AUX}}{N_S}\times\frac{R_{ZCSD}}{R_{ZCSU}+R_{ZCSD}} (11)$$

$$\frac{V_{VIN_OVP}}{V_{OVP}}\geq\frac{N_{AUX}}{N_S} (12)$$

Where V_{OVP} is the output over voltage specification; R_{ZCSU} and R_{ZCSD} compose the resistor divider. The turns ratio of N_S to N_{AUX} and the ratio of R_{ZCSU} to R_{ZCSD} could be induced from equation (11) and (12).

Short Circuit Protection (SCP)

When the output is shorted to ground, the output voltage is clamped to zero. The voltage of the auxiliary winding is proportional to the output winding, so V_{VIN} will drop down without auxiliary winding supply. Once V_{VIN} is below $V_{VIN,OFF}$, the IC will shut down and be charged again by the BUS voltage through the start up resistor. If the short circuit condition still exists, the system will operate in hiccup mode.

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In order to guarantee SCP function not effected by voltage spike of auxiliary winding, a filter resistor R_{AUX} is needed (10Ω typically) shown in Fig.9.

Line regulation modification

The IC provides line regulation modification function to improve line regulation performance.

Due to the sample delay of Source pin and other internal delay, the output current increases with increasing input BUS line voltage. A small compensation voltage ΔV_{SE-C} is added to Source pin during ON time to improve such performance. This ΔV_{SE-C} is adjusted by the upper resistor of the divider connected to ZCS pin.

$$\Delta V_{SE,C} = V_{BUS} \times \frac{N_{AUX}}{N_P} \times \frac{1}{R_{ZCSU}} \times k_2 \quad (13)$$

Where R_{ZCSU} is the upper resistor of the divider; k_2 is an internal constant as the modification coefficient.

The compensation is mainly related with R_{ZCSU}, larger compensation is achieved with smaller R_{ZCSU}. Normally, R_{ZCS} ranges from 100kΩ~1MΩ.

Then R_{ZCSD} can be selected by,

$$\frac{\frac{V_{ZCS_OVP}}{V_{OUT}} \times \frac{N_S}{N_{AUX}}}{1 - \frac{V_{ZCS_OVP}}{V_{OUT}} \times \frac{N_S}{N_{AUX}}} \times R_{ZCSU} > R_{ZCSD} \quad (14),$$

And,

$$R_{ZCSD} \geq \frac{\frac{V_{ZCS_OVP}}{V_{OVP}} \times \frac{N_S}{N_{AUX}}}{1 - \frac{V_{ZCS_OVP}}{V_{OVP}} \times \frac{N_S}{N_{AUX}}} \times R_{ZCSU} \quad (15)$$

Where V_{OVP} is the output over voltage protection specification; V_{OUT} is the rated output voltage; R_{ZCSU} is the upper resistor of the divider; N_S and N_{AUX} are the turns of secondary winding and auxiliary winding separately.

Power design

A few applications are shown as below.

Products	Input range	Output current	Application	Temperature rise
SY58203	90Vac~264Vac	0.3A	5.0W/ER27	25℃
	90Vac~264Vac	0.3A	5.5W/ER27	32℃
	90Vac~264Vac	0.3A	6.5W/ER27	38℃
	90Vac~264Vac	0.3A	7.0W/ER27	43℃

The test is operated in natural cooling condition at 25 ℃ ambient temperature.

Power Device Design

MOSFET and Diode

When the operation condition is with maximum input voltage and full load, the voltage stress of integrated MOSFET and secondary power diode is maximized;

$$V_{MOS_DS_MAX} = \sqrt{2} V_{AC_MAX} + N_{PS} \times (V_{OUT} + V_{D_F}) + \Delta V_S \quad (16)$$

$$V_{D_R_MAX} = \frac{\sqrt{2} V_{AC_MAX}}{N_{PS}} + V_{OUT} \quad (17)$$

Where $V_{AC,MAX}$ is maximum input AC RMS voltage; N_{PS} is the turns ratio of the Flyback transformer; V_{OUT} is the rated output voltage; $V_{D,F}$ is the forward voltage of secondary power diode; ΔV_S is the overshoot voltage clamped by RCD snubber during OFF time.

When the operation condition is with minimum input voltage and full load, the current stress of integrated MOSFET and power diode is maximized.

$$I_{MOS_PK_MAX} = I_{P_PK_MAX} \quad (18)$$

$$I_{MOS_RMS_MAX} = I_{P_RMS_MAX} \quad (19)$$

$$I_{D_PK_MAX} = N_{PS} \times I_{P_PK_MAX} \quad (20)$$

$$I_{D_AVG} = I_{OUT} \quad (21)$$

Where $I_{P\text{-}PK\text{-}MAX}$ and $I_{P\text{-}RMS\text{-}MAX}$ are maximum primary peak current and RMS current, which will be introduced later.

Transformer (N_{PS} and L_M)

N_{PS} is limited by the electrical stress of the internal power MOSFET:

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$$N_{PS} \le \frac{V_{MOS_(BR)DS} \times 80\% - \sqrt{2} V_{AC_MAX} - \Delta V_S}{V_{OUT} + V_{D_F}} \quad (22)$$

Where $V_{MOS,(BR)DS}$ is the breakdown voltage of the integrated MOSFET.

In Quasi-Resonant mode, each switching period cycle t_S consists of three parts: current rising time t_1, current falling time t_2 and quasi-resonant time t_3 shown in Fig.10.

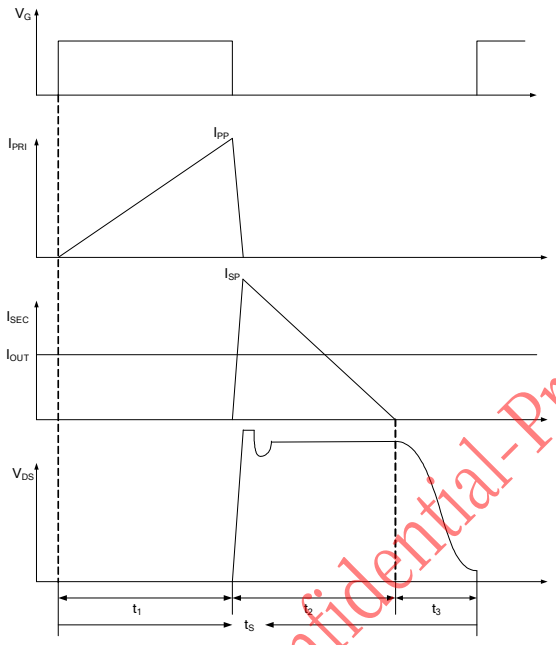


Fig.10 switching waveforms

The system operates in the constant on time mode to achieve high power factor. The ON time increases with the input AC RMS voltage decreasing and the load increasing. When the operation condition is with minimum input AC RMS voltage and full load, the ON time is maximized. On the other hand, when the input voltage is at the peak value, the OFF time is maximized. Thus, the minimum switching frequency $f_{S\text{-}MIN}$ happens at the peak value of input voltage with minimum input AC RMS voltage and maximum load condition; Meanwhile, the maximum peak current through integrated MOSFET and the transformer happens.

Once the minimum frequency $f_{S\text{-}MIN}$ is set, the inductance of the transformer could be induced. The design flow is shown as below:

(a) Select N_{PS}

$$N_{PS} \le \frac{V_{MOS_(BR)DS} \times 80\% - \sqrt{2} V_{AC_MAX} - \Delta V_S}{V_{OUT} + V_{D_F}} \quad (23)$$

(b) Preset minimum frequency $f_{S\text{-}MIN}$

(c) Compute relative t_S, t_1 (t_3 is omitted to simplify the design here)

$$t_S = \frac{1}{f_{S_MIN}} \quad (24)$$

$$t_1 = \frac{t_S \times N_{PS} \times (V_{OUT} + V_{D_F})}{\sqrt{2} V_{AC_MIN} + N_{PS} \times (V_{OUT} + V_{D_F})} \quad (25)$$

(d) Design inductance L_M

$$L_M = \frac{V_{AC_MIN}^2 \times t_1^2 \times \eta}{2 P_{OUT} \times t_S} \quad (26)$$

(e) Compute t_3

$$t_3 = \pi \times \sqrt{L_M \times C_{Drain}} \quad (27)$$

Where C_{Drain} is the parasitic capacitance at drain of integrated MOSFET.

(f) Compute primary maximum peak current $I_{P\text{-}PK\text{-}MAX}$ and RMS current $I_{P\text{-}RMS\text{-}MAX}$ for the transformer fabrication.

$$I_{P_PK_MAX} = \frac{2 P_{OUT} \times [\frac{L_M}{\sqrt{2} V_{AC_MIN}} + \frac{L_M}{N_{PS} \times (V_{OUT} + V_{D_F})}]}{L_M \times \eta} + \frac{\sqrt{4 P_{OUT}^2 \times [\frac{L_M}{\sqrt{2} V_{AC_MIN}} + \frac{L_M}{N_{PS} \times (V_{OUT} + V_{D_F})}]^2 + 4 L_M \times \eta \times P_{OUT} \times t_3}}{L_M \times \eta} \quad (28)$$

Where η is the efficiency; P_{OUT} is rated full load power

Adjust t_1 and t_S to t_1' and t_S' considering the effect of t_3

$$t_S' = \frac{\eta \times L_M \times I_{P_PK_MAX}^2}{4 P_{OUT}} \quad (29)$$

$$t_1' = \frac{L_M \times I_{P_PK_MAX}}{\sqrt{2} V_{AC_MIN}} \quad (30)$$

$$I_{P_RMS_MAX} \approx \sqrt{\frac{t_1'}{6 t_S'}} \times I_{P_PK_MAX} \quad (31)$$

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(g) Compute secondary maximum peak current $I_{S\text{-}PK\text{-}MAX}$ and RMS current $I_{S\text{-}RMS\text{-}MAX}$ for the transformer fabrication.

$$I_{S_PK_MAX} = N_{PS} \times I_{P_PK_MAX} \quad (32)$$

$$t_2' = t_S' - t_1' - t_3 \quad (33)$$

$$I_{S_RMS_MAX} \approx \sqrt{\frac{t_2'}{6t_S'}} \times I_{S_PK_MAX} \quad (34)$$

(h) Make sure that t_1', t_2' , t_3' are not out of the range given in EC table.

Transformer design (N_P,N_S,N_{AUX})

The design of the transformer is similar with ordinary Flyback transformer. the parameters below are necessary:

Necessary parameters	
Turns ratio	N_{PS}
Inductance	L_M
Primary maximum current	$I_{P\text{-}PK\text{-}MAX}$
Primary maximum RMS current	$I_{P\text{-}RMS\text{-}MAX}$
Secondary maximum RMS current	$I_{S\text{-}RMS\text{-}MAX}$

The design rules are as followed:

(a) Select the magnetic core style, identify the effective area A_e.

(b) Preset the maximum magnetic flux ΔB

ΔB=0.22~0.26T

(c) Compute primary turn N_P

$$N_P = \frac{L_M \times I_{P_PK_MAX}}{\Delta B \times A_e} \quad (35)$$

(d) Compute secondary turn N_S

$$N_S = \frac{N_P}{N_{PS}} \quad (36)$$

(e) compute auxiliary turn N_{AUX}

$$N_{AUX} = N_S \times \frac{V_{VIN}}{V_{OUT}} \quad (37)$$

Where V_{VIN} is the working voltage of VIN pin (10V~11V is recommended).

(f) Select an appropriate wire diameter

With $I_{P\text{-}RMS\text{-}MAX}$ and $I_{S\text{-}RMS\text{-}MAX}$, select appropriate wire to make sure the current density ranges from 4A/mm^2 to 10A/mm^2.

(g) If the winding area of the core and bobbin is not enough, reselect the core style, go to **(a)** and redesign the transformer until the ideal transformer is achieved.

Output capacitor C_{OUT}

Preset the output current ripple ΔI_{OUT}, C_{OUT} is induced by

$$C_{OUT} = \frac{\sqrt{(\frac{2I_{OUT}}{\Delta I_{OUT}})^2 - 1}}{4\pi f_{AC} R_{LED}} \quad (38)$$

Where I_{OUT} is the rated output current; ΔI_{OUT} is the demanded current ripple; f_{AC} is the input AC supply frequency; R_{LED} is the equivalent series resistor of the LED load.

RCD snubber for MOSFET

The power loss of the snubber P_{RCD} is evaluated first

$$P_{RCD} = \frac{N_{PS} \times (V_{OUT} + V_{D_F}) + \Delta V_S}{\Delta V_S} \times \frac{L_K}{L_M} \times P_{OUT} \quad (39)$$

Where N_{PS} is the turns ratio of the Flyback transformer; V_{OUT} is the output voltage; $V_{D\text{-}F}$ is the forward voltage of the power diode; ΔV_S is the overshoot voltage clamped by RCD snubber; L_K is the leakage inductor; L_M is the inductance of the Flyback transformer; P_{OUT} is the output power.

The R_{RCD} is related with the power loss:

$$R_{RCD} = \frac{(N_{PS} \times (V_{OUT} + V_{D_F}) + \Delta V_S)^2}{P_{RCD}} \quad (40)$$

The C_{RCD} is related with the voltage ripple of the snubber $\Delta V_{C\text{-}RCD}$:

$$C_{RCD} = \frac{N_{PS} \times (V_{OUT} + V_{D_F}) + \Delta V_S}{R_{RCD} f_S \Delta V_{C_RCD}} \quad (41)$$

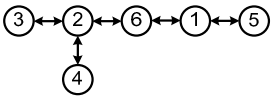
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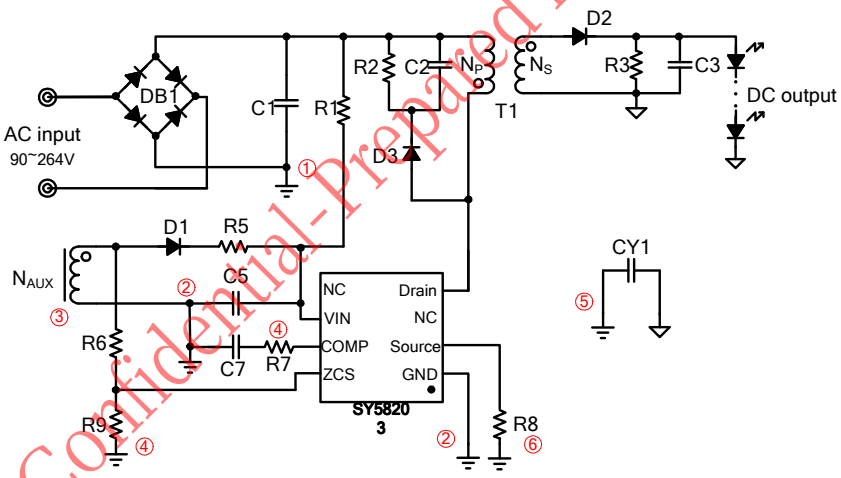
Layout

(a) To achieve better EMI performance and reduce line frequency ripples, the output of the bridge rectifier should be connected to the BUS line capacitor first, then to the switching circuit.

(b) The circuit loop of all switching circuit should be kept small: primary power loop, secondary loop and auxiliary power loop.

(c) The connection of primary ground is recommended as:





Ground ①: ground of BUS line capacitor
Ground ②: ground of bias supply capacitor
Ground ③: ground node of auxiliary winding
Ground ④: ground of signal trace
Ground ⑤: primary ground node of Y capacitor
Ground ⑥: ground node of current sample resistor.

(d) bias supply trace should be connected to the bias supply capacitor first instead of GND pin. The bias supply capacitor should be put beside the IC.

(e) Loop of 'Source pin – current sample resistor – GND pin' should be kept as small as possible.

(f) The resistor divider connected to ZCS pin is recommended to be put beside the IC.

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Design Example

A design example of typical application is shown below step by step.

#1. Identify design specification

Design Specification			
V_{AC}(RMS)	90V~264V	V_{OUT}	24V
I_{OUT}	330mA	η	85%

#2. Transformer design (N_{PS}, L_M)

Refer to Power Device Design

Conditions			
$V_{AC,MIN}$	90V	V_{AC-MAX}	264V
$\triangle V_S$	50V	$V_{MOS-(BR)DS}$	700V
P_{OUT}	8W	$V_{D,F}$	1V
C_{Drain}	100pF	f_{S-MIN}	65kHz

(a) Compute turns ratio N_{PS} first

$$N_{PS} \le \frac{V_{MOS_(BR)DS} \times 80\% - \sqrt{2} V_{AC_MAX} - \Delta V_S}{V_{OUT} + V_{D,F}}$$

$$= \frac{700V \times 0.8 - \sqrt{2} \times 264V - 50V}{24V + 1V}$$

$$= 5.48$$

N_{PS} is set to

$$N_{PS} = 4.5$$

(b)$f_{S,MIN}$ is preset

$$f_{S_MIN} = 65kHz$$

(c) Compute the switching period t_S and ON time t_1 at the peak of input voltage.

$$t_S = \frac{1}{f_{S_MIN}} = 15.3\mu s$$

$$t_1 = \frac{t_S \times N_{PS} \times (V_{OUT} + V_{D_F})}{\sqrt{2} V_{AC_MIN} + N_{PS} \times (V_{OUT} + V_{D_F})}$$

$$= \frac{15.3\mu s \times 4.5 \times (24V + 1V)}{\sqrt{2} \times 90V + 4.5 \times (24V + 1V)}$$

$$= 7.2\mu s$$

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(d) Compute the inductance L_M

$$L_M = \frac{V_{AC_MIN}^2 \times t_1^2 \times \eta}{2P_{OUT} \times t_S}$$

$$= \frac{90V^2 \times 7.2\mu s^2 \times 0.85}{2 \times 8W \times 15.3\mu s}$$

$$= 1.46mH$$

Set

$$L_M = 1.4mH$$

(e) Compute the quasi-resonant time t_3

$$t_3 = \pi \times \sqrt{L_M \times C_{Drain}}$$

$$= \pi \times \sqrt{1.4mH \times 100pF}$$

$$= 1.2\mu s$$

(f) Compute primary maximum peak current $I_{P\text{-}PK\text{-}MAX}$

$$I_{P_PK_MAX} = \frac{2P_{OUT} \times [\frac{L_M}{\sqrt{2}V_{AC_MIN}} + \frac{L_M}{N_{PS} \times (V_{OUT} + V_{D_F})}]}{L_M \times \eta} + \frac{\sqrt{4P_{OUT}^2 \times [\frac{L_M}{\sqrt{2}V_{AC_MIN}} + \frac{L_M}{N_{PS} \times (V_{OUT} + V_{D_F})}]^2 + 4L_M \times \eta \times P_{OUT} \times t_3}}{L_M \times \eta}$$

$$= 0.685A$$

Adjust switching period t_S and ON time t_1 to t_S' and t_1'.

$$t_S' = \frac{\eta \times L_M \times I_{P_PK_MAX}^2}{4P_{OUT}}$$

$$= \frac{0.85 \times 1.4mH \times 0.685A^2}{4 \times 8W}$$

$$= 17.4\mu s$$

$$t_1' = \frac{L_M \times I_{P_PK_MAX}}{\sqrt{2}V_{AC_MIN}}$$

$$= \frac{1.4mH \times 0.69A}{\sqrt{2} \times 90V}$$

$$= 7.59\mu s$$

Compute primary maximum RMS current $I_{P\text{-}RMS\text{-}MAX}$

$$I_{P_RMS_MAX} \approx \sqrt{\frac{t_1'}{6t_S'}} \times I_{P_PK_MAX} = \sqrt{\frac{7.59\mu s}{6 \times 17.4\mu s}} \times 0.685A = 0.185A$$

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(g) Compute secondary maximum peak current and the maximum RMS current.

$I_{S_PK_MAX}=N_{PS}\times I_{P_PK_MAX}=4.5\times 0.685A=3.08A$

$t_2^{'}=t_S^{'}-t_1^{'}-t_3=17.4\mu s-7.59\mu s-1.2\mu s=8.6\mu s$

$$I_{S,RMS,MAX}\approx\sqrt{\frac{t_2'}{6t_S'}}\times I_{S_PK_MAX}=\sqrt{\frac{8.6\mu s}{6\times 17.4\mu s}}\times 3.08A=0.88A$$

#3. Select secondary power diode

(a) Compute the voltage and the current stress of secondary power diode

$$V_{D_R_MAX}=\frac{\sqrt{2}V_{AC_MAX}}{N_{PS}}+V_{OUT}=\frac{\sqrt{2}\times 264V}{4.5}+25V=108V$$

$I_{D_PK_MAX}=N_{PS}\times I_{P_PK_MAX}=4.5\times 0.685A=3.08A$

$I_{D_AVG}=I_{OUT}=0.33A$

#4. Select the output capacitor C_{OUT}

Refer to Power Device Design

Conditions			
I_{OUT}	330mA	ΔI_{OUT}	$0.3I_{OUT}$
f_{AC}	50Hz	R_{LED}	$8\times 1.6\Omega$

The output capacitor is

$$C_{OUT}=\frac{\sqrt{(\frac{2I_{OUT}}{\Delta I_{OUT}})^2-1}}{4\pi f_{AC}R_{LED}}=\frac{\sqrt{(\frac{2\times 0.33A}{0.3\times 0.33A})^2-1}}{4\pi\times 50Hz\times 8\times 1.6\Omega}=820\mu F$$

#5. Design RCD snubber

Refer to Power Device Design

Conditions			
V_{OUT}	24V	ΔV_S	50V
N_{PS}	4.5	L_K/L_M	1%
P_{OUT}	8W		

The power loss of the snubber is

$$P_{RCD}=\frac{N_{PS}\times(V_{OUT}+V_{D_F})+\Delta V_S}{\Delta V_S}\times\frac{L_K}{L_M}\times P_{OUT}=\frac{4.5\times(24V+1V)+50V}{50V}\times 0.01\times 8W=0.26W$$

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The resistor of the snubber is

$$R_{RCD}=\frac{(N_{PS}\times(V_{OUT}+V_{D_F})+\Delta V_S)^2}{P_{RCD}}=\frac{(4.5\times(24V+1V)+50V)^2}{0.26W}=101k\Omega$$

The capacitor of the snubber is

$$C_{RCD}=\frac{N_{PS}\times(V_{OUT}+V_{D_F})+\Delta V_S}{R_{RCD}f_S\Delta V_{C_RCD}}=\frac{4.5\times(24V+1V)+50V}{101k\Omega\times100kHz\times25V}=0.64nF$$

#6. Set VIN pin

Refer to Start up

Conditions			
$V_{BUS-MIN}$	90V× 1.414	$V_{BUS-MAX}$	264V× 1.414
I_{ST}	15μA (typical)	V_{IN-ON}	16V (typical)
$I_{VIN-OVP}$	2mA (typical)	t_{ST}	500ms (designed by user)

(a) R_{ST} is preset

$$R_{ST}<\frac{V_{BUS}}{I_{ST}}=\frac{90V\times1.414}{15\mu A}=8.48M\Omega\ ,$$

$$R_{ST}>\frac{V_{BUS}}{I_{VIN_OVP}}=\frac{264V\times1.414}{2mA}=186k\Omega$$

Set R_{ST}

$$R_{ST}=470k\Omega\times2=940k\Omega$$

(b) Design C_{VIN}

$$C_{VIN}=\frac{(\frac{V_{BUS}}{R_{ST}}-I_{ST})\times t_{ST}}{V_{VIN_ON}}=\frac{(\frac{90V\times1.414}{750k\Omega}-15\mu A)\times500ms}{16V}=4.83\mu F$$

Set C_{VIN}

$$C_{VIN}=10\mu F$$

#7 Set COMP pin

Refer to **Internal pre-charge design for quick start up**

Parameters designed			
R_{COMP}	500Ω	$V_{COMP,IC}$	450mV
C_{COMP1}	2μF	C_{COMP2}	100pF

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#8 Set current sense resistor to achieve ideal output current

Refer to **Primary-side constant-current control**

Known conditions at this step			
k	0.167	N_{PS}	4.5
V_{REF}	0.3V	I_{OUT}	0.33A

The current sense resistor is

$$R_S = \frac{k \times V_{REF} \times N_{PS}}{I_{OUT}} = \frac{0.167 \times 0.3V \times 4.5}{0.33A} = 0.65\Omega$$

#9 set ZCS pin

Refer to **Line regulation modification** and **Over Voltage Protection (OVP) & Open Loop Protection (OLP)**

First identify R_{ZCSU} need for line regulation.

Known conditions at this step			
k_2	68		
Parameters Designed			
R_{ZCSU}	150kΩ		

Then compute R_{ZCSD}

Conditions			
V_{ZCS_OVP}	1.42V	V_{OVP}	30V
V_{OUT}	24V		
Parameters designed			
R_{ZCSU}	150kΩ		
N_S / N_{AUX}	2.4		

$$R_{ZCSD} < \frac{\frac{V_{ZCS_OVP}}{V_{OUT}} \times \frac{N_S}{N_{AUX}}}{1 - \frac{V_{ZCS_OVP}}{V_{OUT}} \times \frac{N_S}{N_{AUX}}} \times R_{ZCSU} = \frac{\frac{1.42V}{24V} \times 2.4}{1 - \frac{1.42V}{24V} \times 2.4} \times 150k\Omega = 24.8k\Omega$$

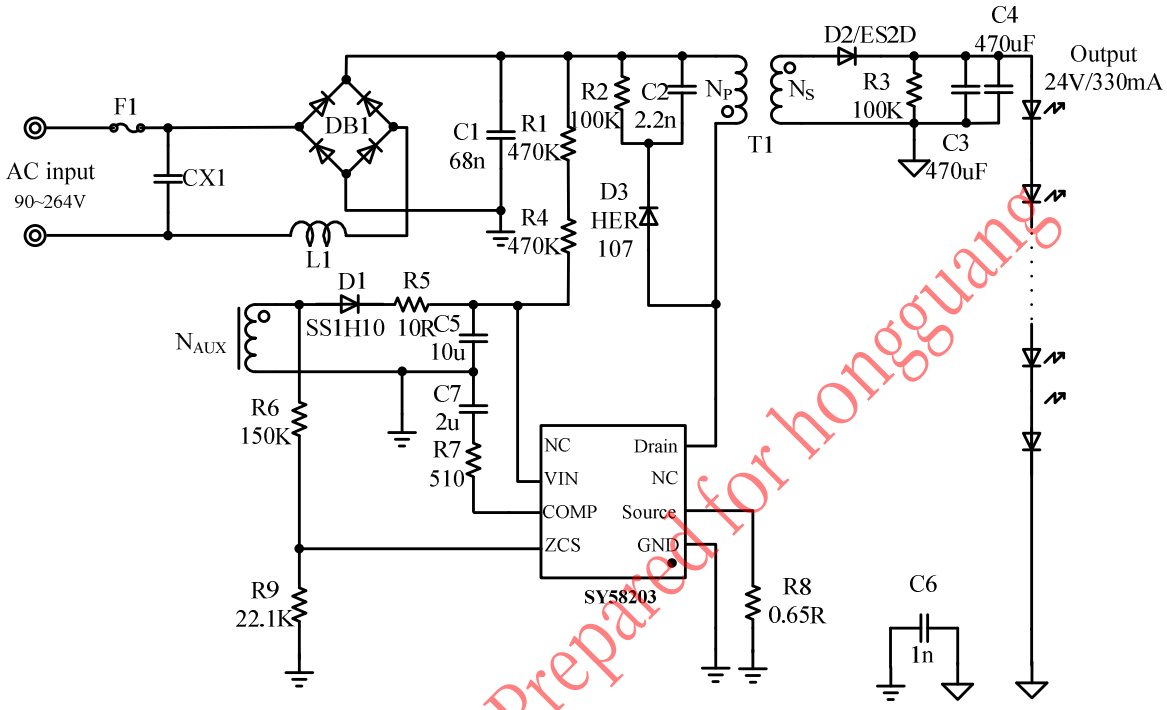
$$R_{ZCSD} \geq \frac{\frac{V_{ZCS_OVP}}{V_{OVP}} \times \frac{N_S}{N_{AUX}}}{1 - \frac{V_{ZCS_OVP}}{V_{OVP}} \times \frac{N_S}{N_{AUX}}} \times R_{ZCSU} = \frac{\frac{1.42V}{30V} \times 2.4}{1 - \frac{1.42V}{30V} \times 2.4} \times 150k\Omega = 19.2k\Omega$$

R_{ZCSD} is set to

$R_{ZCSD} = 22.1k\Omega$

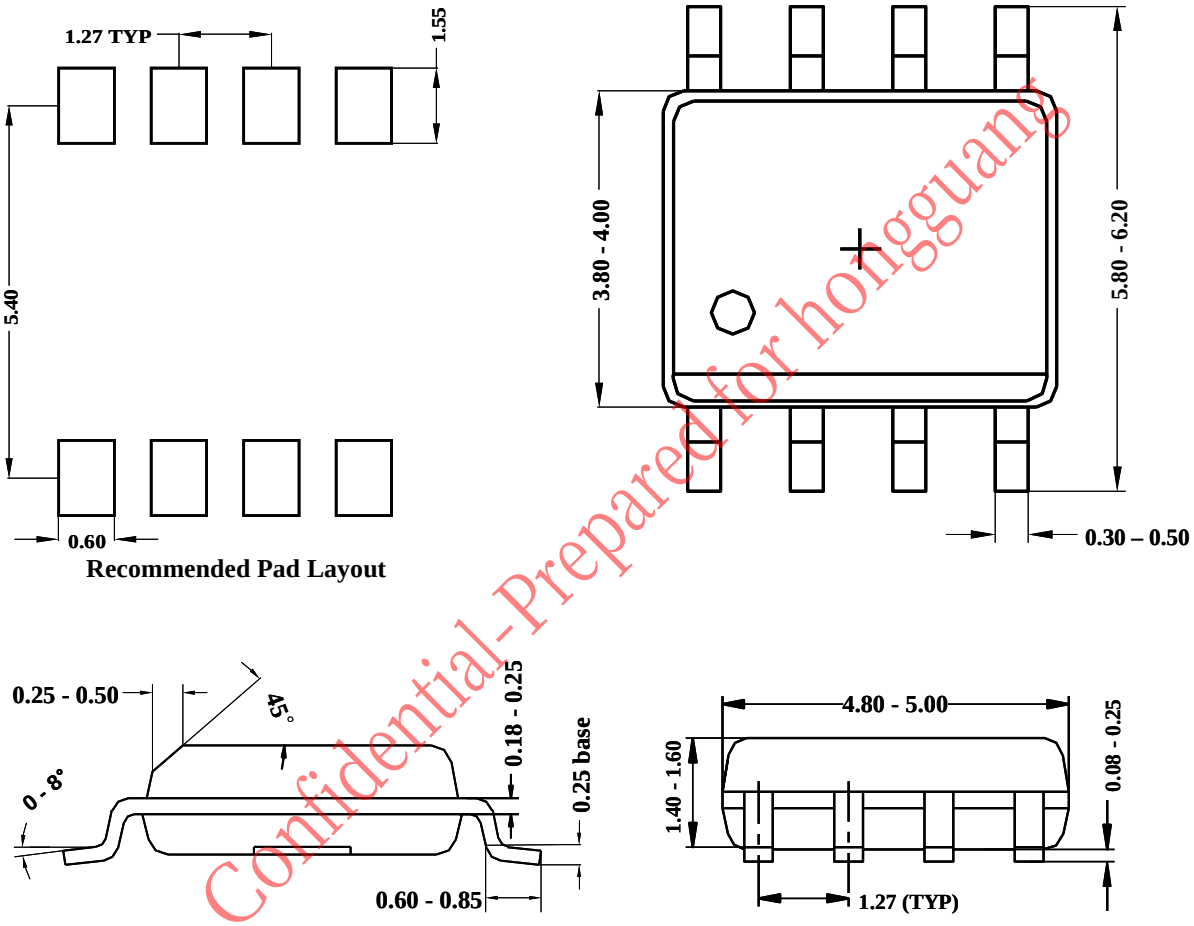
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#10 Final result



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SO8 Package Outline & PCB Layout Design



Recommended Pad Layout

Notes: All dimensions are in millimeters.
All dimensions don't include mold flash & metal burr.

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